Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

NTUD3171PZ

Small Signal MOSFET

−20 V, −200 mA, Dual P−Channel, 1.0 x 1.0 mm SOT−963 Package

ON Semiconductor®

http://onsemi.com

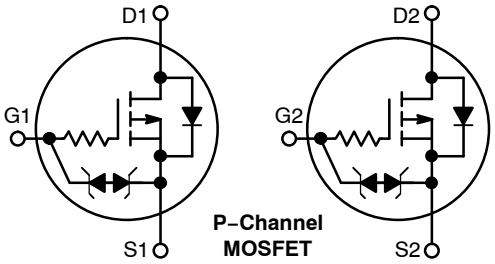
Features

- Dual P−Channel MOSFET
- Offers a Low $R_{DS(on)}$ Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics.
- This is a Pb−Free Device

Applications

- High Side Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Equipment

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D Max
−20 V	5.0 Ω @ −4.5 V	−0.2 A
	6.0 Ω @ −2.5 V	
	7.0 Ω @ −1.8 V	
	10 Ω @ −1.5 V	



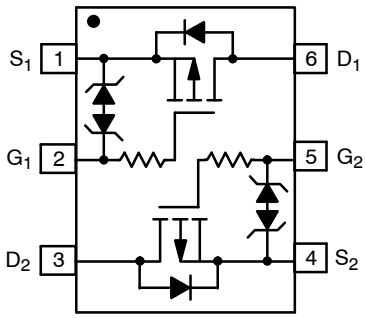
MAXIMUM RATINGS (T_J = 25°C unless otherwise specified)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	−20	V
Gate−to−Source Voltage			V_{GS}	±8	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	−200	mA
		T_A = 85°C		−140	
	t ≤ 5 s	T_A = 25°C		−250	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	−125	mW
	t ≤ 5 s			−200	
Pulsed Drain Current		t_p = 10 μs	I_{DM}	−600	mA
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode) (Note 2)			I_S	−200	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface−mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.
2. Pulse Test: pulse width ≤300 μs, duty cycle ≤2%

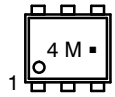
PINOUT: SOT−963



Top View

SOT−963
CASE 527AD

MARKING DIAGRAM



4 = Specific Device Code
M = Date Code
▪ = Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction−to−Ambient − Steady State (Note 3)	$R_{\theta JA}$	1000	°C/W
Junction−to−Ambient − t = 5 s (Note 3)		600	

3. Surface−mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = −5.0 V	T_J = 25°C			−50	nA
		V_{GS} = 0 V, V_{DS} = −5.0 V	T_J = 85°C			−100	
		V_{GS} = 0 V, V_{DS} = −16 V	T_J = 25°C			−200	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±5.0 V				±100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA		−0.4		−1.0	V
Drain−to−Source On Resistance	$R_{DS(ON)}$	V_{GS} = −4.5 V, I_D = −100 mA			2.0	5.0	Ω
		V_{GS} = −2.5 V, I_D = −50 mA			2.6	6.0	
		V_{GS} = −1.8 V, I_D = −20 mA			3.4	7.0	
		V_{GS} = −1.5 V, I_D = −10 mA			4.0	10	
		V_{GS} = −1.2 V, I_D = −1.0 mA			6.0		
Forward Transconductance	g_{FS}	V_{DS} = −5.0 V, I_D = −125 mA			0.35		S
Source−Drain Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −10 mA			−0.6	−1.0	V
CHARGES, CAPACITANCES AND GATE RESISTANCE							
Input Capacitance	C_{ISS}	f = 1 MHz, V_{GS} = 0 V V_{DS} = −15 V			13.5		pF
Output Capacitance	C_{OSS}				3.8		
Reverse Transfer Capacitance	C_{RSS}				2.0		
SWITCHING CHARACTERISTICS, V_{GS} = 4.5 V (Note 4)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −4.5 V, V_{DD} = −15 V, I_D = −200 mA, R_G = 2.0 Ω			26		ns
Rise Time	t_r				46		
Turn−Off Delay Time	$t_{d(OFF)}$				196		
Fall Time	t_f				145		

4. Switching characteristics are independent of operating junction temperatures

ORDERING INFORMATION

Device	Package	Shipping†
NTUD3171PZT5G	SOT−963 (Pb−Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

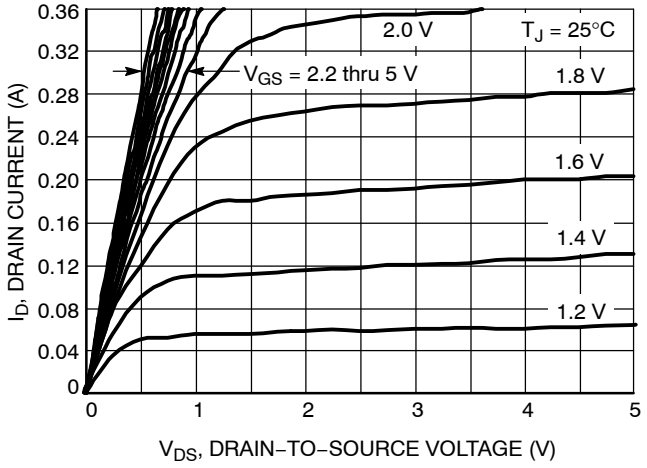


Figure 1. On−Region Characteristics

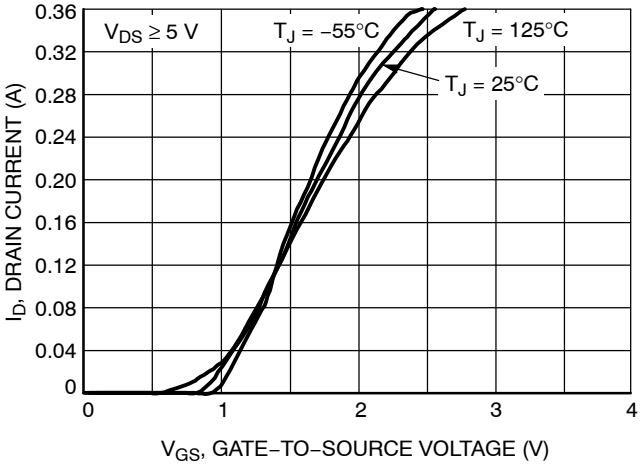


Figure 2. Transfer Characteristics

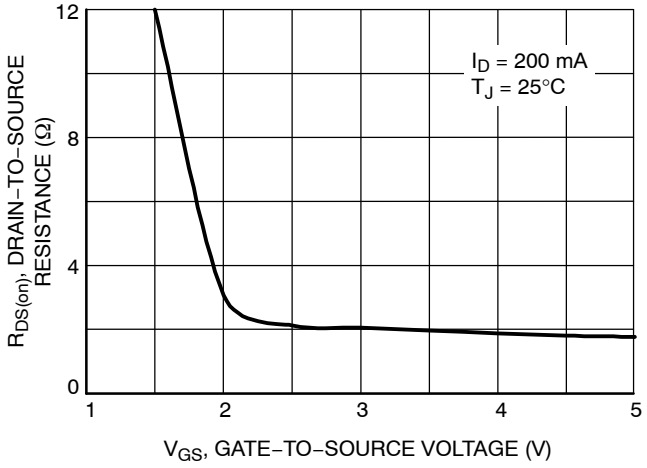


Figure 3. On−Resistance vs. Gate Voltage

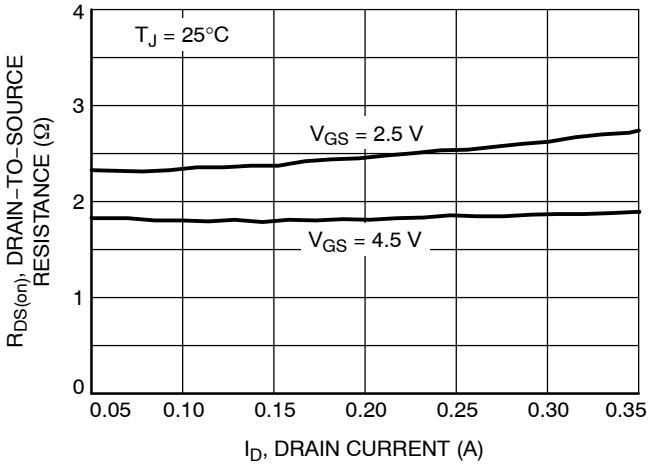


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

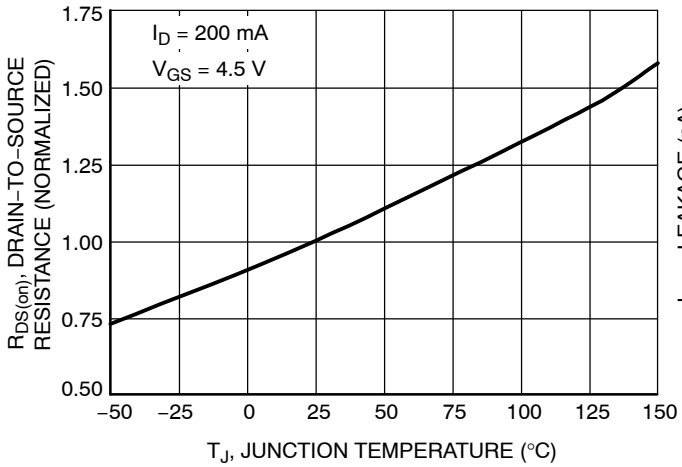


Figure 5. On−Resistance Variation with Temperature

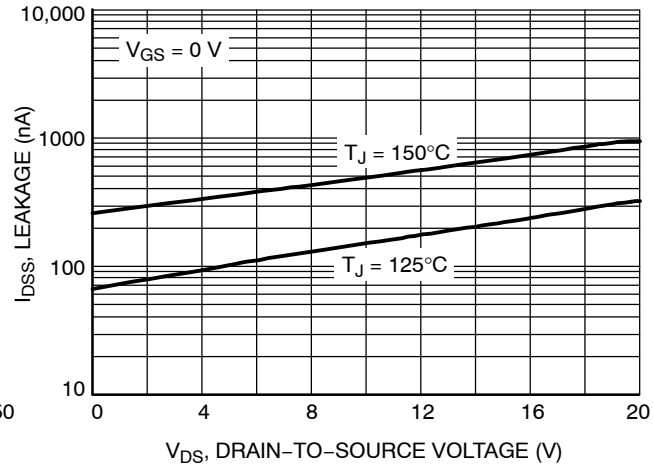


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

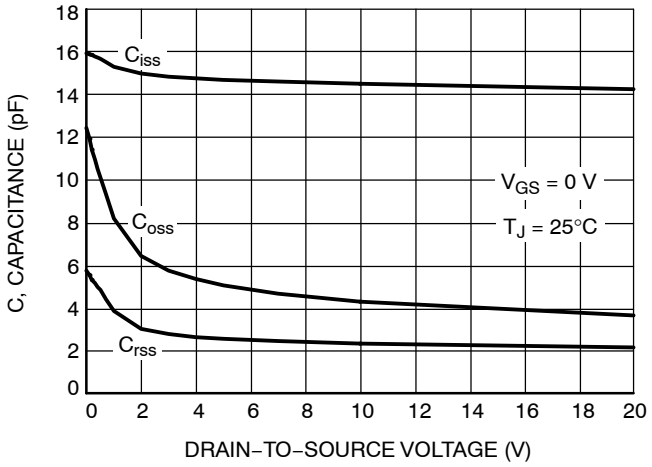


Figure 7. Capacitance Variation

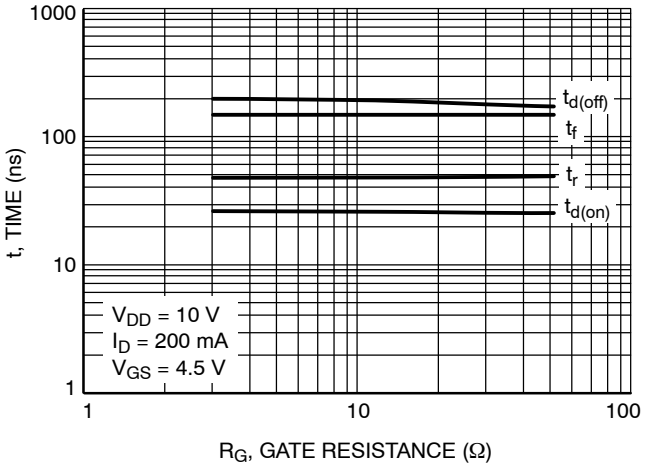


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

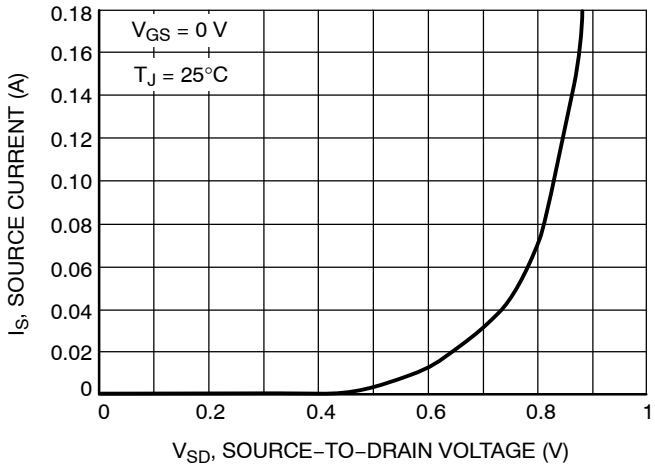
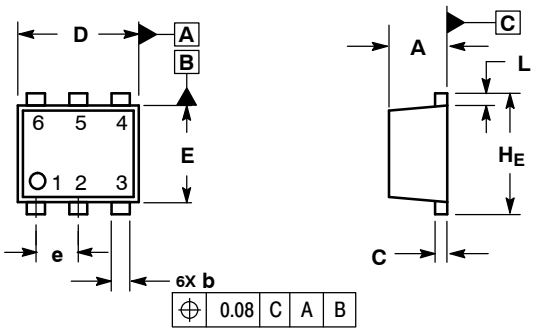


Figure 9. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS

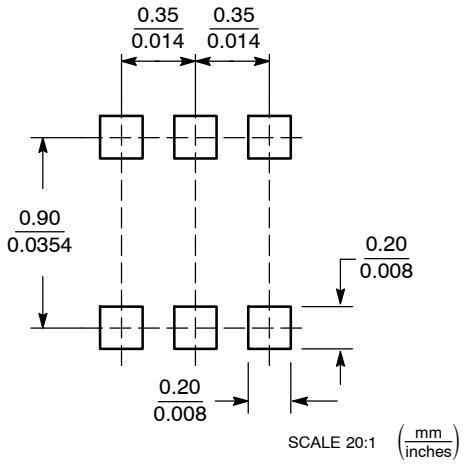
SOT−963
CASE 527AD−01
ISSUE D



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.34	0.37	0.40			
b	0.10	0.15	0.20	0.004	0.006	0.008
C	0.07	0.12	0.17	0.003	0.005	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.75	0.80	0.85	0.03	0.032	0.034
e	0.35 BSC			0.014 BSC		
L	0.05	0.10	0.15	0.002	0.004	0.006
H_E	0.95	1.00	1.05	0.037	0.039	0.041

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
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ON Semiconductor Website: **www.onsemi.com**

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